

## 产品概览

### FCH165N65S3R0: Power MOSFET, N-Channel, SUPERFET® III, Easy Drive, 650 V, 19 A, 165 mΩ, TO-247

欲看完整文档，请参阅数据表。

SUPERFET III MOSFET is ON Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provide superior switching performance, and withstand extreme dv/dt rate. Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

#### 特性

- 700 V @ T<sub>J</sub> = 150 °C
- Low Effective Output Capacitance (Typ. C<sub>oss</sub>(eff.) = 341 pF)
- Ultra Low Gate Charge (Typ. Q<sub>g</sub> = 39 nC)
- Optimized Capacitance
- 100% Avalanche Tested
- RoHS Compliant
- Typ. R<sub>DS(on)</sub> = 140 mΩ
- Internal Gate Resistance: 0.5 Ω

#### 应用

- Telecommunication
- Cloud system
- Industrial

#### 优势

- Higher system reliability at low temperature operation
- Low switching loss
- Low switching loss
- Lower peak V<sub>ds</sub> and lower V<sub>gs</sub> oscillation

#### 终端产品

- Telecom power
- Server power
- EV charger
- Solar / UPS

### 器件电气规格

产品	Pricing (\$/Unit)	Compliance	Status	Channel Polarity	Configuration	V <sub>DSS</sub> (BR) Min (V)	V <sub>GS</sub> Max (V)	V <sub>GS(th)</sub> Max (V)	I <sub>D</sub> Max (A)	P <sub>D</sub> Max (W)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 2.5 V (mΩ)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 4.5 V (mΩ)	R <sub>DS(on)</sub> Max @ V <sub>GS</sub> = 10 V (mΩ)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 4.5 V (nC)	Q <sub>g</sub> Typ @ V <sub>GS</sub> = 10 V (nC)	C <sub>iss</sub> Typ (pF)	Package Type
FCH165N65S3R0-F155	1.4837	Pb-free non AEC-Q and PPAP	Active	N-Channel	Single	650	30	4.5	19	154			165		39		TO-247-3

欲了解更多信息，请联系您当地的销售支援 [www.onsemi.cn](http://www.onsemi.cn)。

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